

L Number	Hits	Search Text	DB	Time stamp
1	240	ma-ching-tien-.in. ma-c-t.in. chen-tsung-chuan-.in. chen-t-c.in. hsu-shew-tsu-.in. hsu-s-t-.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/09 12:45
7	7122	430/311,313,314,317,327,328,330.ccls. 328/694.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/09 12:47
2	8	ma-ching-tien-.in. chen-tsung-chuan-.in. hsu-shew-tsu-.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/09 12:49
3	19	((resist photoresist photo-resist ) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) near (duv! (deep adj2 (uv ultraviolet ultra-violet ultra adj violet)))) same (oxide dioxide) near (layer film coating)) same (etchstop etch-stop etch adj stop hardmask hard-mask hard adj mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/09 12:50
4	26	((resist photoresist photo-resist ) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) with cur\$3) and ((resist photoresist photo-resist ) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) with ((duv! (deep adj2 (uv ultraviolet ultra-violet ultra adj violet))) (krf arf f2 "f.sub.2") (("157" "193" "248") near (nm! nanometer nano-meter nano adj meter)))) and (etchstop etch-stop etch adj stop hardmask hard-mask hard adj mask) with (si silicon si-contain\$3 silicon-contain\$3) ((silicon adj (nitride oxynitride oxy-nitride oxy adj nitride carbide)) "si.sub.3 n.sub.4" sion sic))) and ((oxide dioxide) near (layer film coating))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/09 12:50
5	7	((resist photoresist photo-resist ) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) near (duv! (deep adj2 (uv ultraviolet ultra-violet ultra adj violet)))) with cur\$3 with (light radiation)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/09 12:51
6	13	((duv! (deep adj2 (uv ultraviolet ultra-violet ultra adj violet))) ((uv ultraviolet ultra-violet ultra adj violet) ) near3 cur\$3) with temperature with (time seconds! minute)) same (resist photoresist photo-resist )	USPAT	2003/12/09 12:52
8	8673	(duv! uv ultraviolet ultra-violet ultra adj violet) near3 (resist photoresist photo-resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/09 12:53
9	7783	(etchstop etch-stop etch adj stop) near (layer film coating material)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/09 12:53
10	483449	(si-contain\$3 silicon-contain\$3 (silicon adj (oxide dioxide nitride)) sio sio2 sin sixny si3n4 "sio.sub.2" "si.sub.3 n.sub.4" "si.sub.x n.sub.y")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/09 12:55
11	263896	oxide near (layer film coating material)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/09 12:55

12	2	((duv! uv ultraviolet ultra-violet ultra adj violet) near3 (resist photoresist photo-resist) ) same (((etchstop etch-stop etch adj stop) near (layer film coating material)) with ((si-contain\$3 silicon-contain\$3 (silicon adj (oxide dioxide nitride)) sio sio2 sin sixny si3n4 "sio.sub.2" "si.sub.3 n.sub.4" "si.sub.x n.sub.y")) same (oxide near (layer film coating material))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/09 12:56
13	5	((duv! uv ultraviolet ultra-violet ultra adj violet) near3 (resist photoresist photo-resist) ) same (((etchstop etch-stop etch adj stop) near (layer film coating material)) ) same (oxide near (layer film coating material))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/09 12:56
14	5	((430/311,313,314,317,327,328,330.ccls. 328/694.ccls.) and ((duv! uv ultraviolet ultra-violet ultra adj violet) near3 (resist photoresist photo-resist) ) and (((etchstop etch-stop etch adj stop) near (layer film coating material)) same ((si-contain\$3 silicon-contain\$3 (silicon adj (oxide dioxide nitride)) sio sio2 sin sixny si3n4 "sio.sub.2" "si.sub.3 n.sub.4" "si.sub.x n.sub.y")) and (oxide near (layer film coating material))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/09 12:57